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# Thermodynamic Properties of Gaseous Silicon Monotelluride and the Bond Dissociation Enthalpy $D_m^{\circ}(SiTe)$ at $T \rightarrow 0$

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Statistical-thermodynamic calculations have been combined with the results of high-temperature Knudsen-effusion studies of the vaporization of Si<sub>2</sub>Te<sub>3</sub> to calculate the thermodynamic properties of SiTe(g) from  $T \rightarrow 0$  to T = 2000 K. The dissociation enthalpy  $D_{\rm m}^{\circ}({\rm SiTe}, T \rightarrow 0)$  is  $(448 \pm 8)$  kJ·mol<sup>-1</sup>; its value is discussed vis-à-vis the other silicon monochalcogenides.

Key words: Silicon monotelluride; thermodynamic properties; enthalpy of formation; Gibbs free energy of formation; entropy; enthalpy; heat capacity; dissociation enthalpy.

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#### 1. Introduction

For efficient technological applications of Si<sub>2</sub>Te<sub>3</sub> (see Ref. 1, for example) it is desirable to understand the thermodynamics of its behavior not only at low temperatures, the topic with which our recently described measurements<sup>1</sup> of the standard molar enthalpy of formation  $\Delta_t H_m^{\circ}$ at T = 298.15 K were mostly concerned, but also at high temperatures. According to Exsteen *et al.*,<sup>2</sup> vaporization of Si<sub>2</sub>Te<sub>3</sub> occurs as follows (no value of x was given):

 $Si_2Te_3(cr) = (2-x)Si(cr) + \frac{1}{2}(3-x)Te_2(g) + xSiTe(g).$  (1)

Thus, in addition to the well-established thermodynamic functions of Si(cr)<sup>3</sup> and Te<sub>2</sub>(g),<sup>4</sup> the same quantities, with comparable accuracy, are also required for SiTe(g). At present, those are available only in approximate form, at just a few temperatures, computed on the basis of estimated spectroscopic constants. Thanks to a recent extensive rotational analysis by Gopal and coworkers<sup>5</sup> of the  $A^{1}\Pi - X^{1}\Sigma^{+}$  band system of the emission spectrum of Si<sup>130</sup>Te, the missing spectroscopic information has become available and it is now possible, by means of the well-known formulae of statistical mechanics, to cal-

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culate the thermodynamic properties of SiTe(g) as a function of temperature with the desired high level of reliability.

#### 2. Calculations

Because Gopal et al.5 determined spectroscopic constants for Si<sup>130</sup>Te only, their results were modified by us to refer to SiTe formed from Te of normal isotopic composition, the material encountered in everyday chemical reactions. We used the formulae given by Herzberg,<sup>6</sup> and first calculated the factor  $\rho = \mu(Si^{130}Te) = 0.99839$ , where  $\mu$  denotes the reduced mass of the molecule on the basis of the molar masses of the elements: 28.0855 g·mol<sup>-1</sup> for Si,<sup>7</sup> 127.60 g·mol<sup>-1</sup> for Te of normal isotopic composition,<sup>7</sup> and 129.9062 g·mol<sup>-1</sup> for <sup>130</sup>Te.<sup>8</sup> The following relations from Herzberg<sup>6</sup> were adopted in the present study:  $\omega_e(SiTe) = \omega_e(Si^{130}Te)/\rho; \quad \omega_e x_e(SiTe)$  $\omega_o x_c(\mathrm{Si}^{130}\mathrm{Te})/\rho^2$ ;  $B_c(\mathrm{Si}\mathrm{Te}) = B_c(\mathrm{Si}^{130}\mathrm{Te})/\rho^2$ ;  $\alpha_c(\mathrm{Si}\mathrm{Te}) =$  $\alpha_{\rm e}({\rm Si}^{130}{\rm Te})/\rho^3$ ; and  $D_{\rm e}({\rm Si}{\rm Te}) = D_{\rm e}({\rm Si}^{130}{\rm Te})/\rho^4$ . The resulting adjusted spectroscopic constants (the Gopal et al. values for Si<sup>130</sup>Te are in parentheses) were:  $\omega_e = 481.44$ cm<sup>-1</sup> (480.66 cm<sup>-1</sup>);  $\omega_e x_e = 1.3471$  cm<sup>-1</sup> (1.3428 cm<sup>-1</sup>);  $B_e = 0.14212$  cm<sup>-1</sup> (0.141661 cm<sup>-1</sup>);  $\alpha_e = 0.5353 \cdot 10^{-3}$  $(0.5327 \cdot 10^{-3})$ ; and  $D_e = 0.49 \cdot 10^{-7}$   $(0.49 \cdot 10^{-7})$ . The symmetry number and the ground-state degeneracy of SiTe were each taken to be 1. Values of the physical constants are those recommended by CODATA,<sup>9</sup> with R = 8.31451 $J \cdot K^{-1} \cdot mol^{-1}$ .

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#### 3. Results

Table 1 gives the thermodynamic functions computed with the JANAF program<sup>3</sup> by treating SiTe(g) as an anharmonic oscillator, non-rigid rotor. A state sum program was used in which the contributions to the thermal functions of all vibration-rotation levels up to the dissociation limit ( $\approx 37450 \text{ cm}^{-1}$ ) were included, as was done in the JANAF<sup>3</sup> tables for such molecules as  $H_2$ ,  $D_2$ , HD, and  $N_2$ . Exploratory calculations showed that at  $T \le 2000$  K the effect on the results was negligible when the lowest excited state  $(^{1}\Pi)$  was included. Therefore, the quantities in Table 1 were determined solely on the basis of the ground  $({}^{1}\Sigma^{+})$  electronic state. Also included in the table are values of the standard molar enthalpy of formation,  $\Delta_{f}H_{m}^{\circ}(T)$ , and the standard Gibbs free energy of formation,  $\Delta_f G^{\circ}_m(T)$ . Those quantities have as their bases  $\Delta_{\rm f} H^{\circ}_{\rm m}(298.15 {\rm K})$ , the derivation of which will be discussed in the next section. Thermodynamic functions X in columns 2 through 5 of Table 1 are believed to be uncer tain by no more than  $\pm 0.002 X$ , and both  $\Delta_{\rm f} H^{\circ}_{\rm m}/10^3 \cdot {\rm R} \cdot {\rm K}$ and  $\Delta_f G_m^{\circ}/10^3 \cdot R \cdot K$  are estimated to be uncertain by approximately  $\pm 0.2$ .

#### 4. Discussion

There are differences between the quantities in columns 2 to 5 of Table 1 and those reported by previous investigators, none of whom had access to detailed spectroscopic information on SiTe. Brebrick's<sup>10</sup> values, which he listed at five temperatures only, are quite close to ours and tend to deviate from them by approximately one per cent. This seems to be due, almost entirely, to his use of  $r_e = 0.251$  nm, somewhat greater than the  $r_e = 0.22697$  nm implicit in the measurements of Gopal *et al*. There is similar disagreement with the results of Kelley and King,<sup>11</sup> calculated on the basis of an estimated moment of inertia.

Unlike the conflicting partial pressures,  $p(Te_2)$ , reported by Exsteen *et al.*<sup>2</sup> and Brebrick<sup>10</sup> for the dissociation of Si<sub>2</sub>Te<sub>3</sub> according to:

$$Si_2Te_3(cr) = 2Si(cr) + (3/2)Te_2(g),$$
 (2)

their results for p(SiTe) in the reaction:

$$\operatorname{Si}(\operatorname{cr}) + \frac{1}{2}\operatorname{Te}_2(g) = \operatorname{SiTe}(g)$$
(3)

are in good agreement. For temperatures between 775 K and 950 K, Exsteen *et al.* gave the relation:

$$lg[p(SiTe)/0.1 MPa] = -(12.1 \pm 0.3) \cdot 10^{3} \cdot (K/T) + (8.3 \pm 0.4), \qquad (4)$$

and Brebrick, for  $873 \leq (T/K) \leq 1213$ , reported:

$$lg[p(SiTe)/0.1 \text{ MPa}] = -12.31 \cdot 10^3 \cdot (K/T) + 8.176.$$
 (5)

The dimensionless constant on the right-hand side of Eq. (5) has been modified by us to take into account the new thermodynamic functions for SiTe(g) and the most up-to-date values<sup>4</sup> for Te<sub>2</sub>(g). Exsteen *et al*. and Brebrick did not list experimental pressures at individual tempera-

tures. Accordingly, we have calculated the molar enthalpy change  $\Delta_r H_m^o < T >$  and the molar Gibbs free energy change  $\Delta_r G_m^o < T >$  of reaction (3) from Eqs. (4) and (5) at the mean temperature < T > of each investigation, and used the second- and third-law methods to deduce the enthalpy of the reaction at T = 298.15 K. Auxiliary thermodynamic quantities were taken from Ref. 4 for Te<sub>2</sub>(g); from Ref. 3 for Si(cr); and from Table 1 for SiTe(g).

Results are summarized in Table 2. The mean of the four derived  $\Delta_r H_m^{\circ}s$ , weighted as the inverse of the squares of the uncertainties, is  $<\Delta_r H_m^{\circ}> = (124.9 \pm 1.6)$  kJ·mol<sup>-1</sup>. At the bottom of Table 2 is a Hess cycle that leads to  $D_m^{\circ}(SiTe)$ , the standard molar dissociation enthalpy of SiTe( $^{1}\Sigma^+$ ) at  $T \rightarrow 0$ , where the Si(g) and Te(g) products are each taken to be in their  $^{3}P_2$  ground-state configurations.

In his assessment of the thermochemistry of SiTe,  $Mills^{12}$  listed  $D_m^{\circ}s$  that ranged from 540 kJ·mol<sup>-1</sup> to 430 kJ·mol<sup>-1</sup>, the higher values from extrapolations of spectroscopic information, and the lower, which he favored, from the vaporization studies we have just analyzed. Lakshminarayana and Gopal<sup>13</sup> discussed  $D_m^{\circ}(SiTe)$ . In summary, they gave 550 kJ·mol<sup>-1</sup> (the linear Birge-Sponer extrapolation of  $\omega_0$ ) as the upper limit; estimated 479 kJ·mol<sup>-1</sup> by comparing  $D_m^{\circ}(Si-X)$  for X = O, S, Se, and Te; and regarded Huber and Herzberg's<sup>14</sup> selection of the thermochemical value of 443 kJ·mol<sup>-1</sup> as "some-what low."

As we have seen, second- and third-law treatments of the results of studies<sup>2,10</sup> of the high-temperature vaporization of Si<sub>2</sub>Te<sub>3</sub> yield four values of  $\Delta_t H^{\circ}_{m}$ (SiTe, g, 298.15 K) that are in excellent agreement. Those, in turn, lead to  $D^{\circ}_{m}$ (SiTe) that is close to Huber and Herzberg's<sup>14</sup> choice. It is clear that  $D^{\circ}_{m}$ (SiTe) from thermochemistry is now known with an accuracy of at least  $\pm 10 \text{ kJ} \cdot \text{mol}^{-1}$ . Any diminution of the uncertainty attached to  $\Delta_t H^{\circ}_{m}$ (Si, g), surprisingly large at  $\pm 8 \text{ kJ} \cdot \text{mol}^{-1}$ ,<sup>3</sup> will help define  $D^{\circ}_{m}$ (SiTe) even more precisely.

In an earlier publication,<sup>15</sup> we observed that  $D_m^o(GeX)$ , with X = S, Se, or Te, decreased almost linearly from GeS to GeTe. A comparable trend should occur for  $D_{\rm m}^{\circ}({\rm Si}X)$  because of the similarity in bonding. Gurvich et al.<sup>16</sup> selected  $D_m^{\circ}(SiS) = (613.7 \pm 2.4) \text{ kJ} \cdot \text{mol}^{-1}$  on the basis of a very short extrapolation of vibrational levels of the  $E^{1}\Sigma^{+}$  electronic state, reported<sup>17</sup> up to 50670 cm<sup>-1</sup>, and this value is believed to be reliable. In the case of the selenium analog, the situation is somewhat different. Mills<sup>12</sup> recommended  $D_m^{\circ}(SiSe) = (484 \pm 21) \text{ kJ} \cdot \text{mol}^{-1}$  on the basis of thermochemical measurements and in preference to the spectroscopic value of  $\approx 525 \text{ kJ} \cdot \text{mol}^{-1}$  from the studies of Vago and Barrow<sup>18</sup> as assessed by Gaydon.<sup>19</sup> Subsequently, Huber and Herzberg<sup>14</sup> extrapolated the same vibrational levels of the  $E^{1}\Sigma^{+}$  state and obtained  $D_{\rm m}^{\circ}({\rm SiSe}) = 544 \text{ kJ} \cdot \text{mol}^{-1}$ . In light of the values of  $D_{\rm m}^{\circ}({\rm Ge}X)$ , the spectroscopic  $D_{\rm m}^{\circ}({\rm SiSe})$  appears to be more reasonable than the thermochemical result, even though it incorporates a 90 kJ·mol<sup>-1</sup> extrapolation. Knudseneffusion studies of the high-temperature vaporization

of silicon selenide to SiSe(g) could help resolve the discrepancy. It has been shown<sup>20</sup> that SiSe(cr) cannot be prepared, but an investigation of the high-temperature dissociation of the diselenide [SiSe<sub>2</sub>(cr) + Si(cr) = 2SiSe(g)] has been reported.<sup>21</sup> Results from that study can be used to derive a value of  $\Delta_t H_m^{\circ}(SiSe, g)$  and, thus,  $D_m^{\circ}(SiSe)$ , but a reliable value of  $\Delta_t H_m^{\circ}(SiSe_2, cr,$ 298.15 K), hitherto unavailable, is required. Preliminary measurements<sup>22</sup> of that quantity in progress at this laboratory are in harmony with  $D_m^{\circ}(SiSe) \approx (534 \pm 10)$ kJ·mol<sup>-1</sup>, and thus tend to support the spectroscopic value. If that  $D_m^{\circ}$  is corroborated, then the progression of  $D_m^{\circ}(SiX)$  for X = S, Se, Te will indeed be approximately

From Table 2, we take  $\Delta_r H_m^o(298.15 \text{ K}) = (124.9 \pm 1.6)$ kJ·mol<sup>-1</sup> for reaction (3) and combine it with  $\frac{1}{2}\Delta_r H_m^o$ 

linear, in parallel with  $D_m^{\circ}(\text{Ge}X)$ .

 $(Te_2, g) = (81.6 \pm 0.3) \text{ kJ} \cdot \text{mol}^{-1} \text{ 4 to yield } \Delta_t H^{\circ}_{\text{m}}(\text{SiTe, } g, 298.15 \text{ K}) = (206.5 \pm 1.6) \text{ kJ} \cdot \text{mol}^{-1} \text{ for:}$ 

$$Si(cr) + Te(cr) = SiTe(g).$$
 (6)

This value for the standard molar enthalpy of formation of SiTe(g) agrees within the combined uncertainties with Mills's<sup>12</sup> selection,  $(220 \pm 13)$  kJ·mol<sup>-1</sup>, but is more precise because we have taken a weighted mean for  $\Delta_r H_m^{\circ}$ of reaction (3).

We wish to call attention to  $\Delta_t H_m^{\circ}$  and  $\Delta_t G_m^{\circ}$  in Table 1. Both quantities refer to reaction (3); thus, the thermochemical reference state of tellurium is arbitrarily taken to be  $Te_2(g)$  throughout the entire temperature range of the table.

$\frac{T}{K}$	$\frac{C_{p,\mathbf{m}}^{\circ}}{R}$	$\frac{\Delta_{T'}^{T} H_{m}^{\circ}}{10^{3} \cdot R \cdot K}$	$\frac{\left(\Delta_0^T S_{\rm m}^{\circ} - \Delta_{T'}^T H_{\rm m}^{\circ}/T\right)}{R}$	$\frac{\Delta_0^T S_m^\circ}{R}$	$\frac{\Delta_{\rm f}H_{\rm m}^{\rm o}}{10^3\cdot R\cdot {\rm K}}$	$\frac{\Delta_{\rm f}G_{\rm m}^{\circ}}{10^{3}\cdot R\cdot {\rm K}}$
0	0	- 1.119	∞	0	14.89	14.89
100	3.548	- 0.769	32.822	25.135	15.03	13.89
200	3.904	-0.397	29.683	27.699	15.06	12.74
298.15	4.153	0.000	29.310	29.310	15.02	11.59
300	4.156	0.008	29.310	29.336	15.02	11.58
400	4.286	0.430	29.475	30.551	14.96	10.44
600	4.397	1.301	30.146	32.314	14.81	8.20
800	4.440	2.185	30.854	33.585	14.59	6.04
1000	4.461	3.075	31.503	34.579	14.34	3.93
1200	4.472	3.969	32.086	35.393	14.05	2.87
1400	4.480	4.864	32.609	36.083	13.75	-0.14
1600 <sup>ь</sup>	4.485	5.761	33.081	36.682	13.43	- 2.09
1800	4.488	6.658	33.511	37.210	7.08	- 3.62
2000	4.490	7.556	33.905	37.683	6.81	- 4.77

TABLE 1. Thermodynamic properties of SiTe(g);  $R = 8.31451 \text{ J}\cdot\text{K}^{-1}\cdot\text{mol}^{-1}$ ,  $p^{\circ} = 0.1 \text{ MPa}$ ,  $T' = 298.15 \text{ K}^{*}$ 

<sup>a</sup>Note that  $\Delta_t H_m^\circ$  and  $\Delta_t G_m^\circ$  both refer to the formation reaction: Si(cr or 1) +  $\frac{1}{2}$ Te<sub>2</sub>(g) = SiTe(g), as explained in the text.

"There is a transition at T = 1685 K, the melting temperature of Si.

Reference	Second law $\Delta_r H_r^{\circ}/(kJ \cdot mol^{-1})$	Third law $\Delta_{-}H^{*}/(kJ\cdot mol^{-1})$							
Exsteen et al. <sup>2</sup>	$120.1 \pm 3.0$	127.4±4.5							
Brebrick <sup>10</sup>	$124.6 \pm 2.5$	132.4 ± 4.0							
	$<\Delta_r H_m^\circ> = (124.9 \pm 1.6) \text{ kJ·mol}^{-1a}$								
SiTe(g, $T'$ ) = Si(cr, $T'$ ) + $\frac{1}{2}$ Te <sub>2</sub> (g, $T'$ ),	$\Delta_r H_m^\circ = -(124.9 \pm 1.6) \text{ kJ} \cdot \text{mol}^{-1}$	a							
$\frac{1}{2}Te_2(g, T') = Te(g, T'),$ Si(or T') = Si(o T')	$\Delta_{\rm r} H_{\rm m}^{\rm a} = (127.9 \pm 0.5) \text{ kJ·mol}^{-1 \text{ b}}$								
$Te(g, T') = Te(g, T \rightarrow 0)$	$\Delta_r H_m^{\circ} = (450 \pm 8) \text{ kJ} \cdot \text{mol}^{-1} \text{ c}^{-1}$								
$Si(g, T') = Si(g, T \rightarrow 0),$	$\Delta_r H_m^{-1} = -(7.6 \pm 0.3) \text{ kJ} \cdot \text{mol}^{-1} \text{ c}$								
$SiTe(g, T \rightarrow 0) = SiTe(g, T'),$	$\Delta_{\rm r} H_{\rm m}^{\circ} = (9.3 \pm 0.3)  \rm kJ \cdot mol^{-1}  d$								
$\overline{\operatorname{SiTe}(g,T\to 0)}=\operatorname{Si}(g,T\to 0)+\operatorname{Te}(g,T\to 0),$	$\overline{\Delta_r H_m^\circ = D_m^\circ(\text{SiTe}) = (448 \pm 8) \text{ k}}$	J·mol <sup>-1</sup> °							

TABLE 2. Enthalpy of the reaction: Si(cr) +  $\frac{1}{2}Te_2(g) = SiTe(g)$  at T' = 298.15 K and  $p^\circ = 0.1$  MPa, and derivation of  $D_m^\circ(SiTe)$ 

"Weighted mean of the four values at the top of the table, as discussed in text.

<sup>b</sup>Reference 4.

<sup>c</sup>Reference 3.

<sup>d</sup>Table 1.

•For the dissociation of  $SiTe(^{1}\Sigma)$  to  $Si(^{3}P)$  and  $Te(^{3}P)$ .

#### 5. Acknowledgment

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### 6. References

- <sup>1</sup>P. A. G. O'Hare, G. A. Hope, C. E. Beck, III, J. Chem. Thermodyn. **25**, 919 (1993).
- <sup>2</sup>G. Exsteen, J. Drowart, A. Vander Auwera-Mahieu, R. Callaerts, J.Phys. Chem. **71**, 4130 (1967).
- <sup>3</sup>M. W. Chase, Jr., C. A. Davies, J. R. Downey, Jr., D. J. Frurip, R. A. McDonald, A. N. Syverud, JANAF Thermochemical Tables. Third Edition. J.Phys. Chem. Ref. Data 14 (1985), Supplement no. 1.
- <sup>4</sup>F. Grφnvold, J. Drowart, E. F. Westrum, Jr., The Chemical Thermodynamics of Actinide Elements and Compounds. Part 4. The Actinide Chalcogenides (Excluding Oxides). International Atomic Energy Agency, Vienna (1984).
- <sup>5</sup>S. Gopal, M. Singh, G. Lakshminarayana, Can. J. Phys. 70, 291 (1992).

- <sup>6</sup>G. Herzberg, Molecular Spectra and Molecular Structure. I. Spectra of Diatomic Molecules. Second Edition. (Van Nostrand, New York, 1950).
- <sup>7</sup>Pure Appl. Chem. 63, 975 (1991).
- <sup>8</sup>Pure Appl. Chem. 56, 695 (1984).
- <sup>o</sup>E. R. Cohen, B. N. Taylor, J. Phys. Chem. Ref. Data 17, 1795 (1988).
- <sup>10</sup>R. F. Brebrick, J. Chem. Phys. **49**, 2584 (1968).
- <sup>11</sup>K. K. Kelley, E. G. King, U.S. Bur. Mines, Bull. 592 (1961).
- <sup>12</sup>K. C. Mills, Thermodynamic Data for Inorganic Sulphides, Selenides, and Tellurides (Butterworth, London, 1974).
- <sup>13</sup>G. Lakshminarayana, S. Gopal, Pramána 35, 519 (1990).
- <sup>14</sup>K. P. Huber, G. Herzberg, Molecular Spectra and Molecular Structure. IV. Constants of Diatomic Molecules (Van Nostrand, New York, 1979).
- <sup>15</sup>P. A. G. O'Hare, J. Chem. Thermodyn. 18, 555 (1986).
- <sup>16</sup>Thermodynamic Properties of Individual Substances, Volume 2, Part One. L. V. Gurvich, I. V. Veyts, C. B. Alcock, editors. (Hemisphere, New York, 1991). p. 292.
- <sup>17</sup>S. J. Q. Robinson, R. F. Barrow, Proc. Phys. Soc. London A67, 95 (1954).
- <sup>18</sup>E. E. Vago, R. F. Barrow, Proc. Phys. Soc. London 58, 538 (1946).
- <sup>19</sup>A. G. Gaydon, Dissociation Energies and Spectra of Diatomic Molecules (Chapman and Hall, London, 1968).
- <sup>20</sup>S. Susman, Argonne National Laboratory, personal communication.
- <sup>21</sup>H.-H. Emons, L. Theisen, Monatsh. Chem. 62, 103 (1972).
- <sup>22</sup>I. Tomaszkiewicz, P. A. G. O'Hare, unpublished results.